



## SEARCHED

Class	Sub.	Date	Exmr.
257	288 327 402 405 410 411	7/13/02	A.M
438	287 585 591 778 785 786		
438	216 287 591 785	8/08/03	A.M
257	324 296 327 411		

## INTERFERENCE SEARCHED

Class	Sub.	Date	Exmr.

## SEARCH NOTES (INCLUDING SEARCH STRATEGY)

	Date	Exmr.
IEEE: MOSFET + Ta <sub>2</sub> O <sub>5</sub> + Oxynitride	7/13/02	A.M
EAST: US-PUB-EPD JP-Derwent CCLS; MOSFET + High-K or high permittivity - Zirconium and Hafnium and Oxynitride		
EAST (ALL) * Inventors ✓ * Metal + Silicate + gate dielectric	8/07/03	A.M